

11/27/01  
30135 U.S. PAT. & T.M. OFF. #

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE  
REQUEST FOR FILING APPLICATION UNDER 37 C.F.R. 1.53(b)  
WITHOUT FILING FEE AND/OR WITHOUT EXECUTED INVENTOR'S DECLARATION

Assistant Commissioner for Patents  
Washington, DC 20231

Atty. Dkt. 925-219

Date: November 27, 2001

This is a request for filing a new PATENT APPLICATION under Rule 53(b) entitled:  
**METHOD FOR MANUFACTURING NONVOLATILE SEMICONDUCTOR MEMORY WITH NARROW VARIATION IN THRESHOLD VOLTAGES OF MEMORY CELLS**

without a filing fee and/or without an executed inventor's oath/declaration.

This application is made by the below identified inventor(s). Attached hereto are the following papers:

Newly executed Declaration,  Copy of Declaration from prior application,  Abstract  
26 pages of specification and claims (including 4 numbered claims), and  
10 sheets of accompanying drawing/s.

Record the attached assignment and return to the undersigned.

Attached is a Power of Attorney.

Priority is hereby claimed under 35 U.S.C. § 119 based on the following foreign applications:

Application Number	Country	Day/Month/Year Filed
2000-361152	Japan	28/11/2000

, respectively, the entire content of which is hereby incorporated by reference in this application..

Certified copy(ies) of foreign application(s) is/are attached.

Certified copy(ies) filed on \_\_\_\_\_ in prior application no. \_\_\_\_\_ filed \_\_\_\_\_

Please amend the specification by inserting the following paragraph before the first line: --This application claims the benefit of Provisional Application No. \_\_\_\_\_, filed \_\_\_\_\_, the entire content of which is hereby incorporated by reference in this application.--

Please amend the specification by inserting the following paragraph before the first line: --This application is a  continuation/ division/ continuation-in-part of Application No. \_\_\_\_\_, filed \_\_\_\_\_, the entire content of which is hereby incorporated by reference in this application.--

Petition filed in prior application to extend its life to insure co-pendency.

The prior application is assigned to \_\_\_\_\_

It is hereby requested that the Examiner consider the art cited in the above parent application(s) by applicant and/or the Examiner for the reasons stated therein. A listing of that art is attached, but pursuant to Rule 98(d) copies are not required.

Applicant claims "small entity" status.  "Small entity" statement attached.

Please enter the attached and/or below preliminary amendment prior to calculation of filing fee:

Also attached:  Information Disclosure Statement;  Non-Publication Request;  Nucleotide and/or Amino Acid Sequence Submission;  Statement deleting Inventor(s) named in prior application;  Other:

1. Inventor: Satoru YAMAGATA Japanese  
(first) MI (last) (citizenship)  
Residence: (city) Hiroshima-ken (state/country) Japan  
Mailing Address: 2537-306, Urakami, Kasuga-cho, Fukuyama-shi, Hiroshima-ken, Japan  
(Zip Code) \_\_\_\_\_

2. Inventor: Masanori YOSHIMI Japanese  
(first) MI (last) (citizenship)  
Residence: (city) Hiroshima-ken (state/country) Japan  
Mailing Address: 3-7-16, Ootanidai, Fukuyama-shi, Hiroshima-ken, Japan  
(Zip Code) \_\_\_\_\_

See attached sheet(s) for additional inventor(s) information!!

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By Atty: H. Warren Burnam, Jr., Reg. No. 29,366

Signature: 